

LIXYS

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Schottky Diode Gen²

High Performance Schottky Diode Low Loss and Soft Recovery Single Diode

Part number

DSA 300 I 45 NA



2 2 1

45 V

300 A

0.70 V

Backside: Isolated

Features / Advantages:

- Very low Vf
- Extremely low switching losses
- low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package:

 $V_{RRM} =$

 $I_{FAV} =$

FN E72873

- Housing: SOT-227B (minibloc)
- Industry standard outline
- Cu base plate internal DCB isolated
- Isolation Voltage 3000 V
- Epoxy meets UL 94V-0
- RoHS compliant

Ratings

Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RRM}	max. repetitive reverse voltage		T _{VJ} = 25°C			45	V
I _R	reverse current	V _R = 45 V	$T_{VJ} = 25^{\circ}C$			1	mA
		V _R = 45 V	$T_{VJ} = 150$ °C			10	mA
V _F	forward voltage	I _F = 300 A	$T_{VJ} = 25^{\circ}C$			0.79	V
		I _F = 600 A				1.02	V
		I _F = 300 A	$T_{VJ} = 125$ °C			0.70	V
		I _F = 600 A				0.97	V
I _{FAV}	average forward current	rectangular d = 0.5	$T_{c} = 95^{\circ}C$			300	Α
V _{F0}	threshold voltage	sulation only	T _{VJ} = 150°C			0.42	V
r _F	slope resistance for power loss calculation only					0.85	m_Ω
R _{thJC}	thermal resistance junction to case					0.20	K/W
T _{VJ}	virtual junction temperature			-40		150	°C
P _{tot}	total power dissipation		$T_{c} = 25^{\circ}C$			750	W
I _{FSM}	max. forward surge current	t = 10 ms (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			5300	Α
C¹	junction capacitance	$V_R = 5V$; $f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		17.0		nF





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Ratings

Symbol	Definition	Condition	S		min.	typ.	max.	Unit
I _{RMS}	RMS current	per termin	al 1)				150	Α
RthCH	thermal resistance case to he	atsink				0.10		K/W
T _{stg}	storage temperature				-40		150	°C
Weight						30		g
M _D	mounting torque				1.1		1.5	Nm
\mathbf{M}_{T}	terminal torque				1.1		1.5	Nm
V _{ISOL}	isolation voltage	t = 1 secor	nd		3000			V
		t = 1 minut	te		2500			V
d _{Spp/App}	creepage striking distance of	on surface through air	terminal to terminal	10.5	3.2			mm
d _{Spb/Apb}	creepage striking distance of	on surface through air	terminal to backside	8.6	6.8			mm

¹⁾ I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

Part number

D = Diode

S = Schottky Diode

A = low VF

300 = Current Rating [A]

I = Single Diode

45 = Reverse Voltage [V]

NA = SOT-227B (minibloc)

ogo → □IXYS abcde ← Part No. YYWWZ XXXXXX

Assembly Code

Product Marking

Assembly Line

DateCode

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DSA 300 I 45 NA	DSA300I45NA	Tube	10	511251

Similar Part	Package	Voltage class
DSA300I100NA	SOT-227B (minibloc)	100
DSA300I200NA	SOT-227B (minibloc)	200

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